## imall

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December 2001

### FDN306P

FAIRCHILD SEMICONDUCTOR

#### P-Channel 1.8V Specified PowerTrench<sup>®</sup> MOSFET

#### **General Description**

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

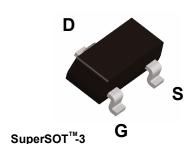
#### Applications

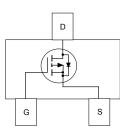
- Battery management
- Load switch
- Battery protection

#### Features

```
• -2.6 A, -12 V. R_{DS(ON)} = 40 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}
R_{DS(ON)} = 50 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}
R_{DS(ON)} = 80 \text{ m}\Omega @ V_{GS} = -1.8 \text{ V}
```

- Fast switching speed
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- SuperSOT<sup>TM</sup> -3 provides low R<sub>DS(ON)</sub> and 30% higher power handling capability than SOT23 in the same footprint





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#### Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-12	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	-2.6	A
	– Pulsed		-10	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		–55 to +150	°C
Therma	I Characteristics			
R <sub>0JA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W

#### Package Marking and Ordering Information

Thermal Resistance, Junction-to-Case

 Device Marking	Device	Reel Size	Tape width	Quantity
306	FDN306P	7"	8mm	3000 units

(Note 1)

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 $R_{\theta JC}$ 

°C/W

FDN306P

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	I				
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V$ , $I_D = -250 \mu A$	-12			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 µA,Referenced to 25°C		-3		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -10 V$ , $V_{GS} = 0 V$			-1	μA
I <sub>GSSF</sub>	Gate–Body Leakage, Forward	$V_{GS} = 8 V$ , $V_{DS} = 0 V$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -8 V$ , $V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	-0.4	-0.6	-1.5	V
<u>ΔVGS(th)</u> ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D$ = –250 µA,Referenced to 25°C		2.5		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$ \begin{array}{l} V_{GS} = -4.5 \ V,  I_D = -2.6 \ A \\ V_{GS} = -2.5 \ V,  I_D = -2.3 \ A \\ V_{GS} = -1.8 \ V,  I_D = -1.8 \ A \\ V_{GS} = -4.5 \ V, \ I_D = -2.6 \ A, \ T_J = 125^\circ C \end{array} $		30 39 54 40	40 50 80 54	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$	-10			А
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5 V$ , $I_D = -2.6 A$		10		S
Dvnamio	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -6 V$ , $V_{GS} = 0 V$ ,		1138		pF
Coss	Output Capacitance	f = 1.0 MHz		454		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			302		pF
Switchin	g Characteristics (Note 2)	•				
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD} = -6 V$ , $I_D = -1 A$ ,		11	20	ns
tr	Turn–On Rise Time	$V_{DD} = -6 V$ , $I_D = -1 A$ , $V_{GS} = -4.5 V$ , $R_{GEN} = 6 \Omega$		10	20	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			38	61	ns
t <sub>f</sub>	Turn–Off Fall Time			35	56	ns
Qg	Total Gate Charge	$V_{DS} = -6 V$ , $I_D = -2.6 A$ ,		12	17	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 V$		2		nC
Q <sub>gd</sub>	Gate–Drain Charge			3		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings	•	•		
l <sub>s</sub>	Maximum Continuous Drain–Sourc				-0.42	А
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$ , $I_S = -0.42$ (Note 2)		-0.6	-1.2	V

R<sub>8JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8JC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.

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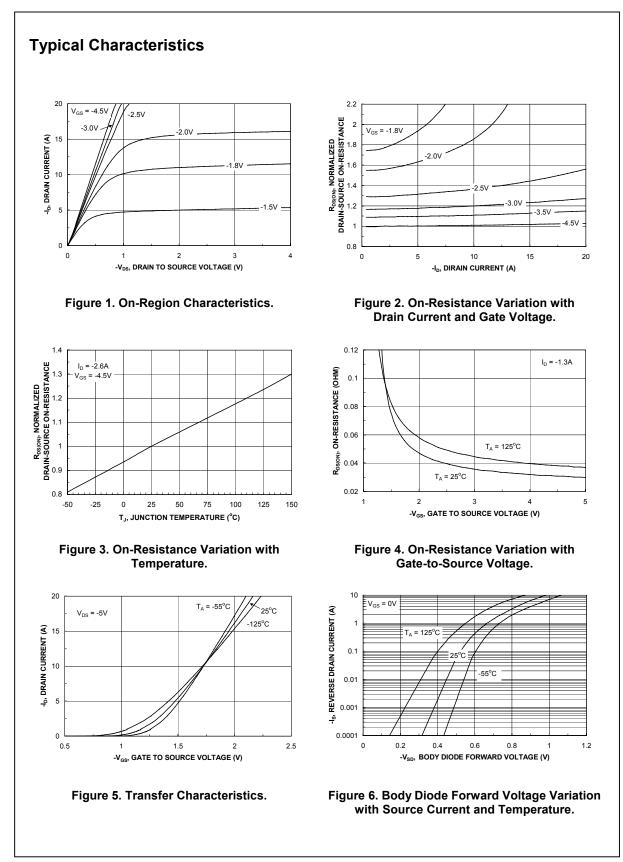
a) 250°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz. copper.

b) 270°C/W when mounted on a minimum pad.

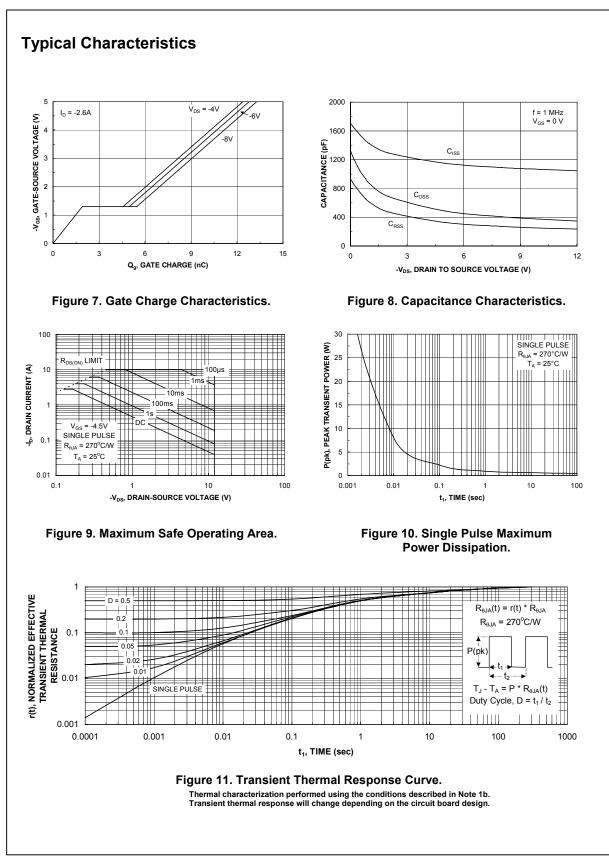
Scale 1 : 1 on letter size paper

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2. Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$ 



FDN306P



# FDN306P

FDN306P Rev D W)

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